FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

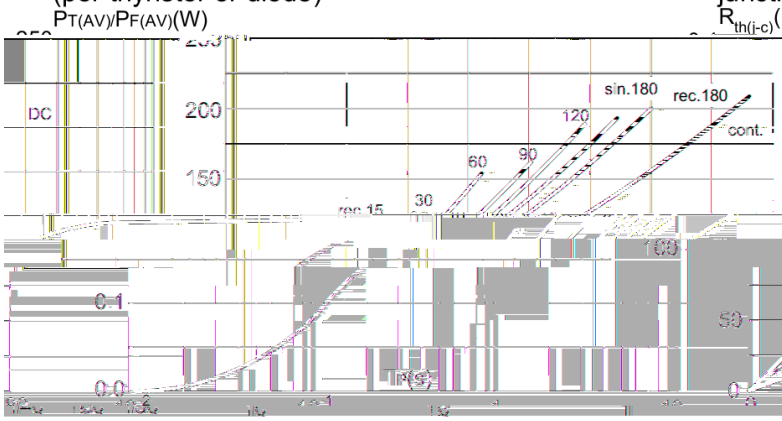


FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

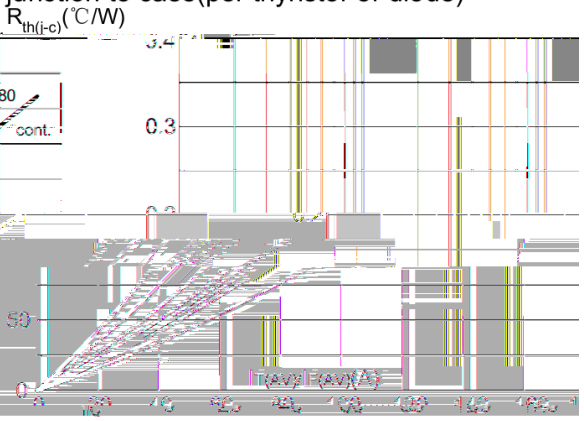


FIG.3: Forward characteristics (per thyristor or diode)

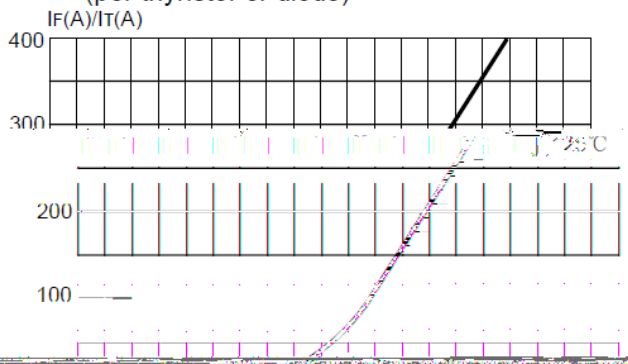


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

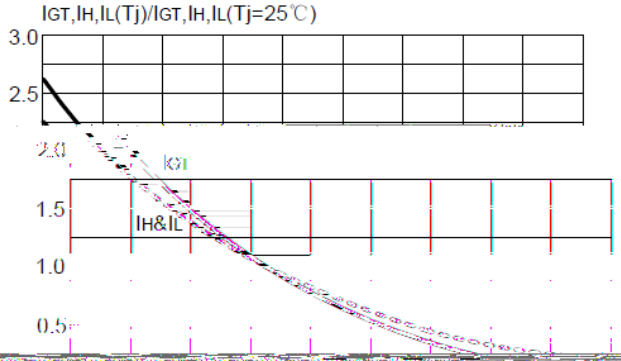


FIG.5 Gate trigger characteristics

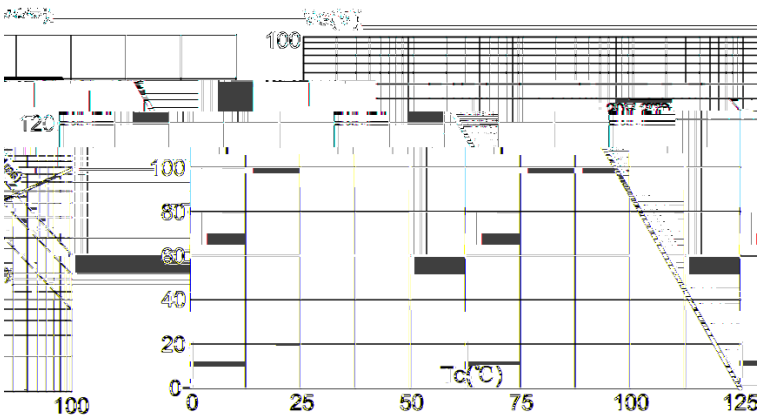
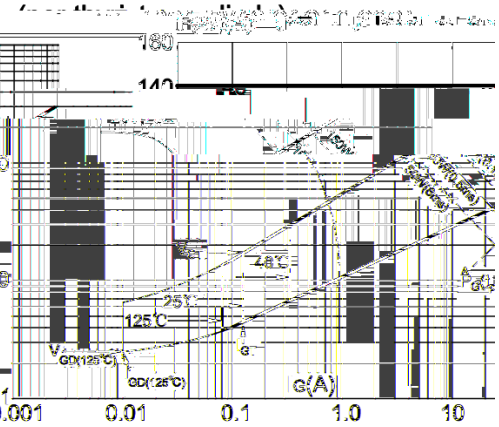
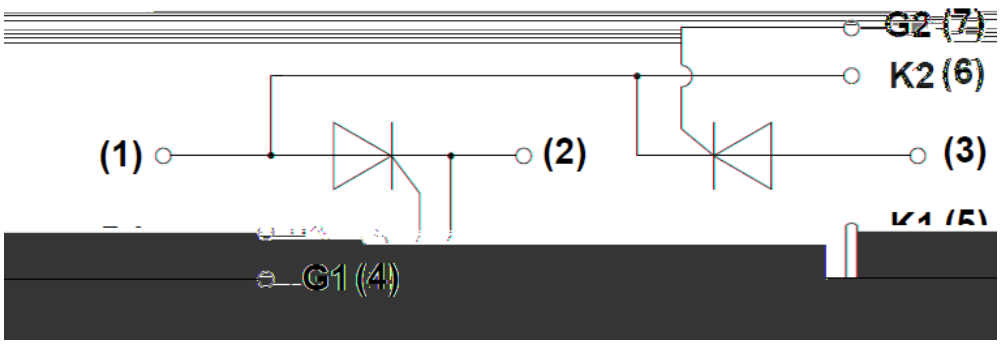
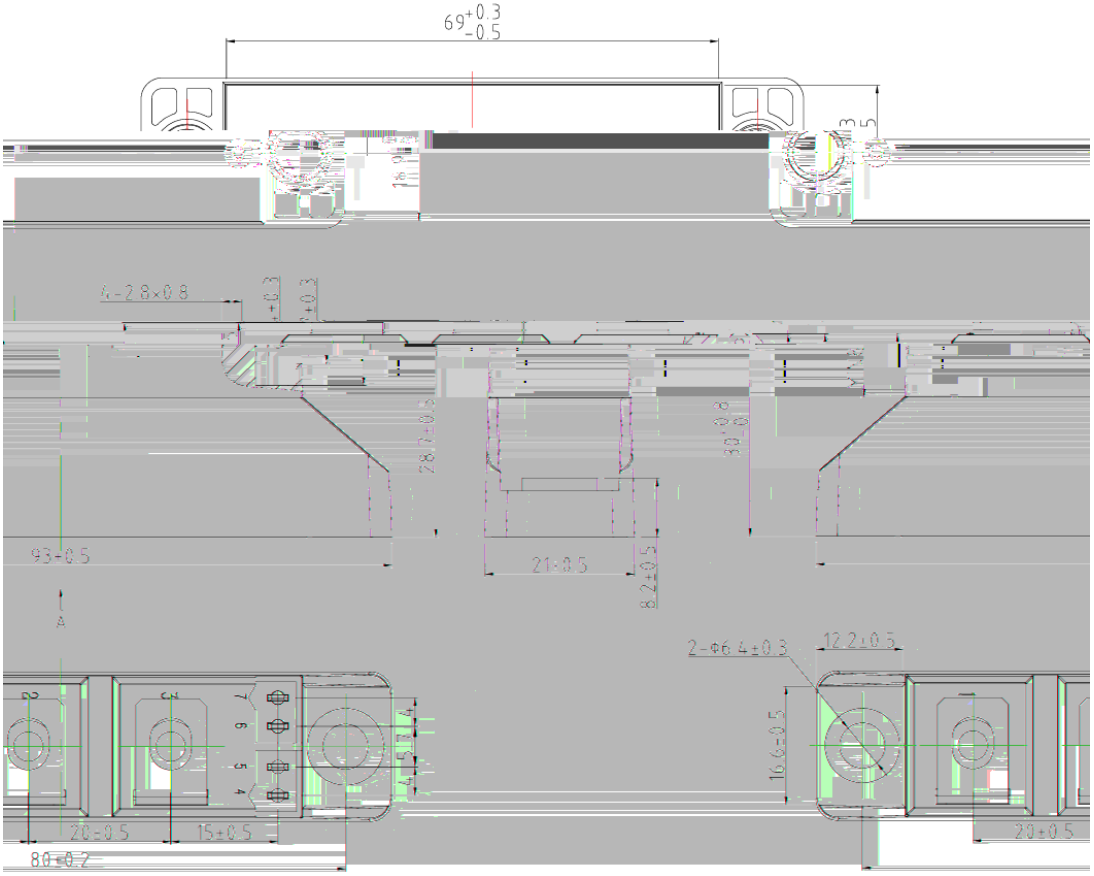


FIG.6: Forward current vs. case temperature




G2 (7)
K2 (6)
(1)
(2)
(3)
G1 (4)


69+0.3 -0.5
4-2.8×0.8
93±0.5
21±0.5
8.2±0.5
2-φ6.4±0.3
12.2±0.5
16.6±0.5
20±0.5
15±0.5
80±0.7